TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (Ultra-High-Speed U-MOSIII)

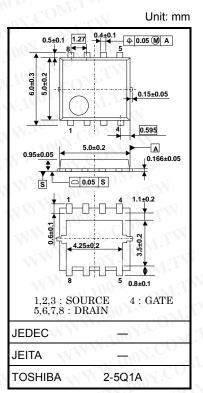
TPCA8014-H

High-Efficiency DC / DC Converter Applications Notebook PC Applications Portable Equipment Applications

- Small footprint due to a small and thin package
- High-speed switching
- Small gate charge: Qsw = 7.4 nC (typ.)
- Low drain-source ON-resistance: $RDS(ON) = 7.1 \text{ m}\Omega$ (typ.)
- High forward transfer admittance: $|Y_{fs}| = 47 \text{ S (typ.)}$
- Low leakage current: $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 40 \text{ V)}$
- Enhancement mode: $V_{th} = 1.1 \text{ to } 2.3 \text{ V (VDS} = 10 \text{ V, ID} = 1 \text{ mA)}$

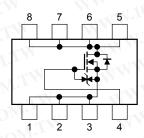
Absolute Maximum Ratings (Ta = 25°C)

		-13.5		
Charac	teristic	Symbol	Rating	Unit
Drain-source voltag	e	V _{DSS}	40	V
Drain-gate voltage	$(R_{GS} = 20 \text{ k}\Omega)$	V _{DGR}	40	V
Gate-source voltage	e M.TW	V _{GSS}	±20	V
Drain current	DC (Note 1)	I _D	30	A 1
Diam current	Pulsed (Note 1)	I _{DP}	90	CAN
Drain power dissipa	ation (Tc = 25°C)	PD	45	W
Drain power dissipa	(t = 10 s) (Note 2a)	₩ P _D	2.8	w
Drain power dissipa	(t = 10 s) (Note 2b)	P _D	1.6	W
Single-pulse avalar	iche energy (Note 3)	E _{AS}	84	mJ
Avalanche current	100Y.	lar	30	A
Repetitive avalanch	e energy (Tc=25°C) (Note 4)	E _{AR}	2.7	mJ
Channel temperatu	re	T _{ch}	150	°C
Storage temperatur	e range	T _{stg}	-55 to 150	°C



Weight: 0.068 g (typ.)

Circuit Configuration



Note: For Notes 1 to 5, refer to the next page.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

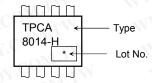
This transistor is an electrostatic-sensitive device. Handle with care.



Thermal Characteristics

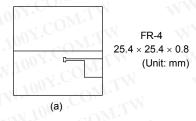
Characteristic	Symbol	Max	Unit
Thermal resistance, channel to case (Tc=25°C)	R _{th (ch-c)}	2.78	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	R _{th (ch-a)}	44.6	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R _{th (ch-a)}	78.1	°C/W

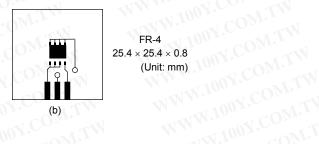
Marking (Note 5)



- Note 1: The channel temperature should not exceed 150°C during use.
 - Note 2: (a) Device mounted on a glass-epoxy board (a)

(b) Device mounted on a glass-epoxy board (b)





- Note 3: $V_{DD} = 24~V,~T_{ch} = 25^{\circ}C$ (initial), L = 0.1 mH, R_G = 25 $\Omega,$ I_{AR} = 30 A
- Note 4: Repetitive rating: pulse width limited by max channel temperature
- Note 5: * Weekly code: (Three digits)

Week of manufacture
(01 for first week of year, continuing up to 52 or 53)

Year of manufacture

(The last digit of the calendar year)

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Cr Cr	naracteristic	Symbol	Test Condition	Min	Тур.	Max	U
Gate leakage cu	rrent	I _{GSS}	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0 \text{ V}$	100	11	±10	μ
Drain cutoff curre	ent	I _{DSS}	$V_{DS} = 40 \text{ V}, V_{GS} = 0 \text{ V}$		TIN	10	μ
Desire VALLE	L. S. W. W.	V (BR) DSS	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	40	VT.	_	,
Drain-source bre	akdown voltage	V (BR) DSX	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	25	100	N —	٧
Gate threshold v	oltage	V _{th}	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$	1.1	DVF.	2.3	٧
		1007.	$V_{GS} = 10 \text{ V}, I_D = 15 \text{ A}$	1	7.1	9.0	
Drain-source ON	i-resistance	R _{DS} (ON)	$V_{GS} = 4.5 \text{ V}, I_D = 15 \text{ A}$	$00\overline{x}$.	10.5	14	mg
Forward transfer	admittance	Y _{fs}	$V_{DS} = 10 \text{ V}, I_D = 15 \text{ A}$	24	47	T	S
Input capacitanc	e VVV	C _{iss}	OTHER WINNE	400	1365	-	
Reverse transfer	capacitance	C _{rss}	V 10 V V 0 V f 1 MHz	1.10	110	Nr.	pF
Output capacitar	nce	C _{oss}	$-V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	M_{II}	480	0M.,	
Gate resistance	TIM I	R _g	COM.TW	1 1. 1	1.0	04/	Ω
.100Y.CO	Rise time	W tr. 100	10 V □ I _D = 15 A	N V	5	ceM	T
Switching time	Turn-on time	ton	V _{GS} 0 V V _{OUT}	WY	110	1.CO	ns
Switching time	Fall time	t _f	8 = 1.33Ω	N.A.	410	01.C	OM
WW.100X	Turn-off time	t _{off}	$V_{DD} \simeq 20 \text{ V}$ Duty \leq 1%, $t_W =$ 10 μs	<u> </u>	18	10 <u>0</u> 1.	
Total gate charge		OVV	$V_{DD} \simeq 32 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}$	-	22	<u></u>	C
(gate-source plus	s gate-drain)	Qg	$V_{DD} \simeq 32 \; V, \; V_{GS} = 5 \; V, \; I_D = 30 \; A$	_	12	1.10	v.C
Gate-source cha	rge 1	Q _{gs1}	MAY TON TOWN	_	5.1	VIII	nC
Gate-drain ("Mille	er") charge	Q _{gd}	$V_{DD} \simeq 32 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}$	_	4.9	1. 10	nr.
Gate switch char	ge N	Q _{SW}	TW TOOY.CO		7.4	= 1	00

Source-Drain Ratings and Characteristics (Ta = 25°C)

WWW.100Y.

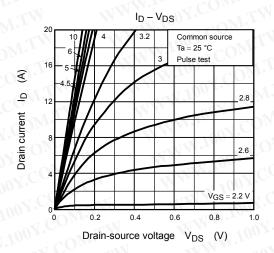
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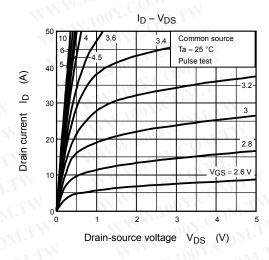
Character	istic	Symbol	Test Condition	Min	Тур.	Max	Unit
Drain reverse current	Pulse (Note 1)	I _{DRP}	WW. TOOX.	W.T.	_	90	Α
Forward voltage (diode)	ON CO.	VDSF	I _{DR} = 30 A, V _{GS} = 0 V	W.	_	-1.2	V

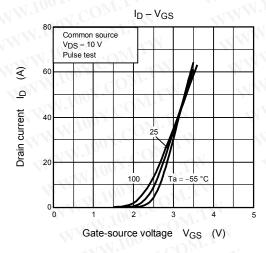
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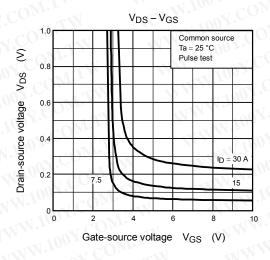
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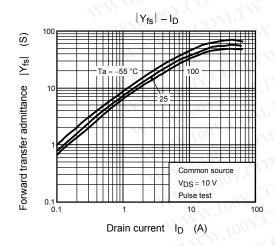
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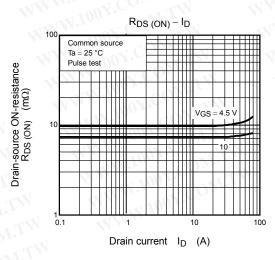


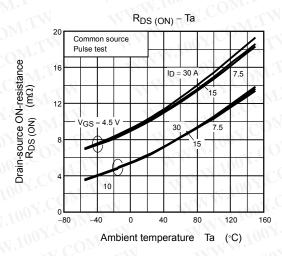


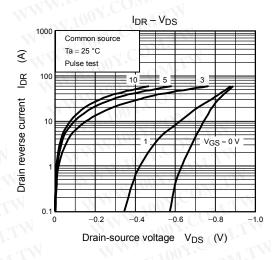


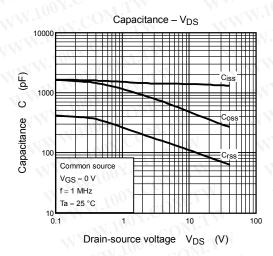


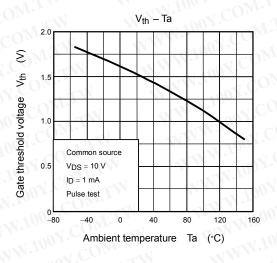


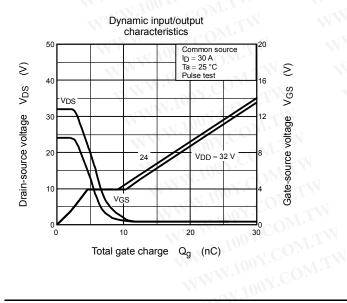


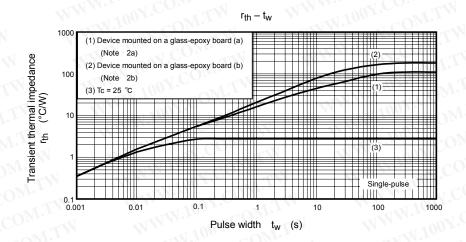


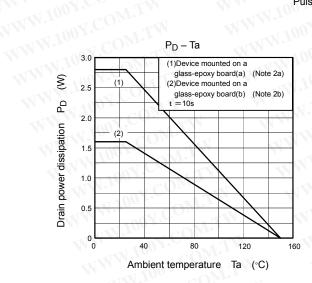


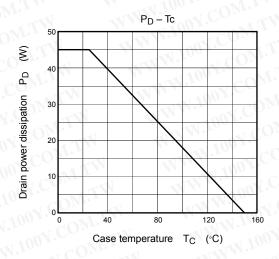


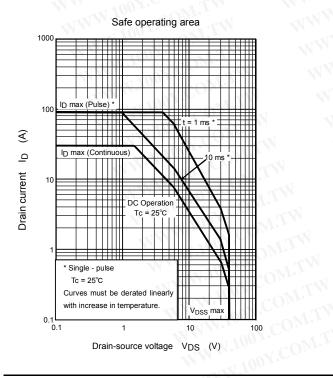












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